

SUBSTITUTE AMENDMENT UNDER 37 C.F.R. § 1.116
Application No.: 10/658,372

Attorney Docket No.: Q77434

AMENDMENTS TO THE ABSTRACT OF THE DISCLOSURE

Please replace the present Abstract with the following amended Abstract:

A reflection mask blank and a method of producing a reflection type mask blank by forming, on a substrate, at least a multilayer reflection film for reflecting exposure light and an absorber layer formed on the multilayer reflection film for absorbing the exposure light, is characterized in that, in order to avoid mixing at an interface between respective layers forming change over lapsed time in properties of the multilayer reflection film due to thermal factors after deposition of the multilayer reflection film, the substrate with the multilayer reflection film is subjected to heat treatment. The heat treatment is during deposition and/or after deposition of the multilayer reflection films so as to suppress the progress of the mixing at the interface between the respective layers. A reflection mask is made from the reflection mask blank according to a reflection mask production method and a semiconductor is made from the reflection mask according to a semiconductor production method.